

MR27V12800J

8M-Word × 16-Bit or 16M-Word × 8-Bit P2ROM

FEATURES

- 8,388,608-word × 16-bit/16,777,216-word × 8-bit electrically switchable configuration
- 3.0 V to 3.6 V power supply
- Access time 80 ns MAX (MR27V12800J-xxxTN)
 100 ns MAX (MR27V12800J-xxxTNE)
- Operating current 25 mA MAX (5MHz)
- Standby current 10 μA MAX
- Input/Output TTL compatible
- Three-state output

PACKAGES

- MR27V12800J-xxxTN, MR27V12800J-xxxTNE
48-pin plastic TSOP (TSOP I 48-P-1220-0.50-1K)
- MR27V12800J-xxxTY, MR27V12800J-xxxTYE
48-pin plastic TSOP (TSOP I 48-P-1220-0.50-L)

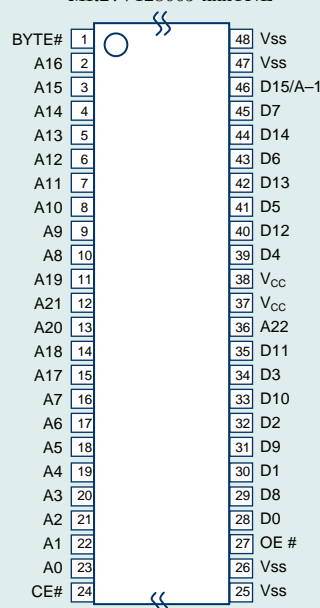
P2ROM ADVANCED TECHNOLOGY

P2ROM stands for Production Programmed ROM. This exclusive LAPIS Semiconductor's technology utilizes factory test equipment for programming the customers code into the P2ROM prior to final production testing. Advancements in this technology allows production costs to be equivalent to MASKROM and has many advantages and added benefits over the other non-volatile technologies, which include the following;

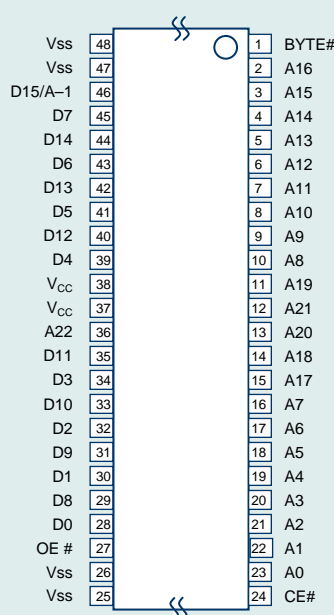
- **Short lead time**, since the P2ROM is programmed at the final stage of the production process, a large P2ROM inventory "bank system" of un-programmed packaged products are maintained to provide an aggressive lead-time and minimize liability as a custom product.
- **No mask charge**, since P2ROMs do not utilize a custom mask for storing customer code, no mask charges apply.
- **No additional programming charge**, unlike Flash and OTP that require additional programming and handling costs, the P2ROM already has the code loaded at the factory with minimal effect on the production throughput. The cost is included in the unit price.
- **Custom Marking is** available at no additional charge.
- **Pin Compatible with Mask ROM**

PIN CONFIGURATION (TOP VIEW)

MR27V12800J-xxxTN
MR27V12800J-xxxTNE



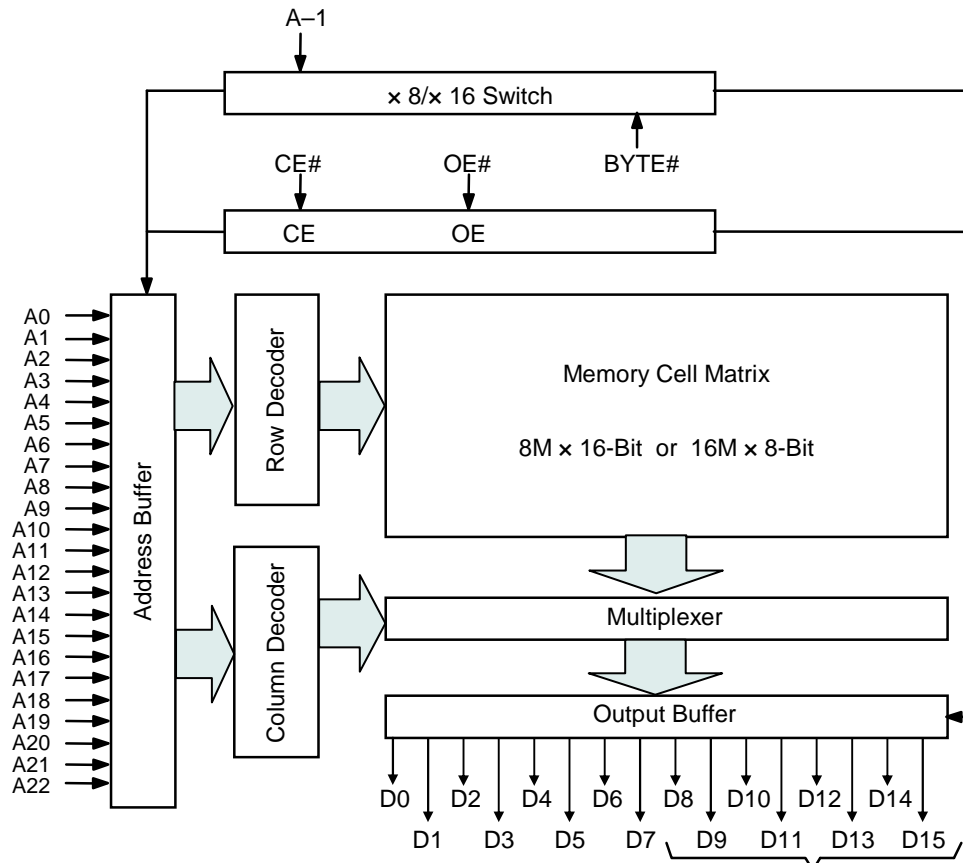
MR27V12800J-xxxTY
MR27V12800J-xxxTYE



48TSOP(Type-I)



BLOCK DIAGRAM



In 8-bit output mode, these pins are placed in a high-Z state and pin D15 functions as the A-1 address pin.

PIN DESCRIPTIONS

Pin name	Functions
D15 / A-1	Data output / Address input
A0 to A22	Address inputs
D0 to D14	Data outputs
CE#	Chip enable input
OE#	Output enable input
BYTE#	Word / Byte select input
V _{CC}	Power supply voltage
V _{SS}	Ground

FUNCTION TABLE

Mode	CE#	OE#	BYTE#	V _{CC}	D0 to D7	D8 to D14	D15/A-1
Read (16-Bit)	L	L	H	3.0 V to 3.6 V	D _{OUT}		
Read (8-Bit)	L	L	L		D _{OUT}	Hi-Z	L/H
Output disable	L	H	H		Hi-Z		
			L		*		
Standby	H	*	H		Hi-Z		
			L		*		

*: Don't Care (H or L)

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Value	Unit
Operating temperature under bias	T _a	—	0 to 70	°C
Storage temperature	T _{stg}		-55 to 125	°C
Input voltage	V _I	relative to V _{SS}	-0.5 to V _{CC} +0.5	V
Output voltage	V _O		-0.5 to V _{CC} +0.5	V
Power supply voltage	V _{CC}		-0.5 to 5	V
Power dissipation per package	P _D	T _a = 25°C	1.0	W
Output short circuit current	I _{OS}	—	10	mA

RECOMMENDED OPERATING CONDITIONS

(T_a = 0 to 70°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
V _{CC} power supply voltage	V _{CC}	V _{CC} = 3.0 to 3.6 V	3.0	—	3.6	V
Input "H" level	V _{IH}		V _{CC} +0.5*	V		
Input "L" level	V _{IL}		-0.5**	—	0.6	V

Voltage is relative to V_{SS}.* : V_{CC}+1.5V(Max.) when pulse width of overshoot is less than 10ns.

** : -1.5V(Min.) when pulse width of undershoot is less than 10ns.

PIN CAPACITANCE

(V_{CC} = 3.0 V, T_a = 25°C, f = 1 MHz)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input	C _{IN1}	V _I = 0 V	—	—	8	pF
BYTE#	C _{IN2}		—	—	200	
Output	C _{OUT}	V _O = 0 V	—	—	10	

ELECTRICAL CHARACTERISTICS**DC Characteristics**(V_{CC} = 2.7 to 3.6 V, Ta = 0 to 70°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input leakage current	I _{LI}	V _I = 0 to V _{CC}	—	—	5	μA
Output leakage current	I _{LO}	V _O = 0 to V _{CC}	—	—	5	μA
V _{CC} power supply current (Standby)	I _{CCSC}	CE# = V _{CC}	—	—	10	μA
	I _{CCST}	CE# = V _{IH}	—	—	1	mA
V _{CC} power supply current (Read)	I _{CCA}	CE# = V _{IL} , OE# = V _{IH} f=5MHz			25	mA
Input "H" level	V _{IH}	—	2.2	—	V _{CC} +0.5*	V
Input "L" level	V _{IL}	—	-0.5**	—	0.6	V
Output "H" level	V _{OH}	I _{OH} = -1 mA	2.4	—	—	V
Output "L" level	V _{OL}	I _{OL} = 2 mA	—	—	0.4	V

Voltage is relative to V_{SS}.* : V_{CC}+1.5V(Max.) when pulse width of overshoot is less than 10ns.

** : -1.5V(Min.) when pulse width of undershoot is less than 10ns.

AC Characteristics

Note 1 → MR27V12800J-xxxTN, MR27V12800J-xxxTY

Note 2 → MR27V12800J-xxxTNE, MR27V12800J-xxxTYE

(V_{CC} = 3.0 to 3.6 V, Ta = 0 to 70°C)

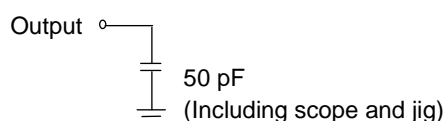
Parameter	Symbol	Condition	Min.	Max.	Unit
Address cycle time	t _C	—	80 (Note 1) 100 (Note 2)	—	ns
Address access time	t _{ACC}	CE# = OE# = V _{IL}	—	80 (Note 1) 100 (Note 2)	ns
CE# access time	t _{CE}	OE# = V _{IL}	—	80 (Note 1) 100 (Note 2)	ns
OE# access time	t _{OE}	CE# = V _{IL}	—	30	ns
Output disable time	t _{CHZ}	OE# = V _{IL}	0	20	ns
	t _{OHZ}	CE# = V _{IL}	0	20	ns
Output hold time	t _{OH}	CE# = OE# = V _{IL}	0	—	ns

Measurement conditions

Input signal level ----- 0 V/3 V

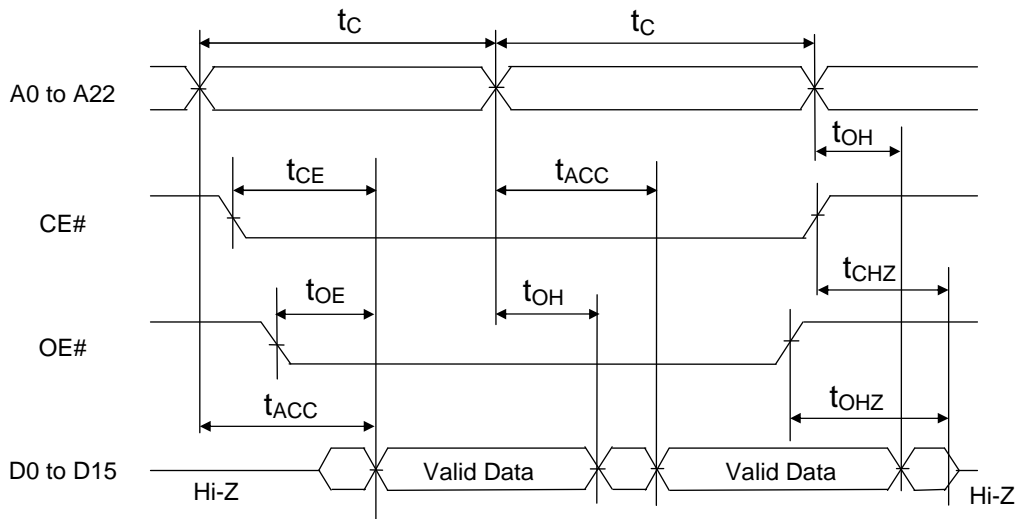
Input timing reference level----- 1/2V_{CC}

Output load ----- 50 pF

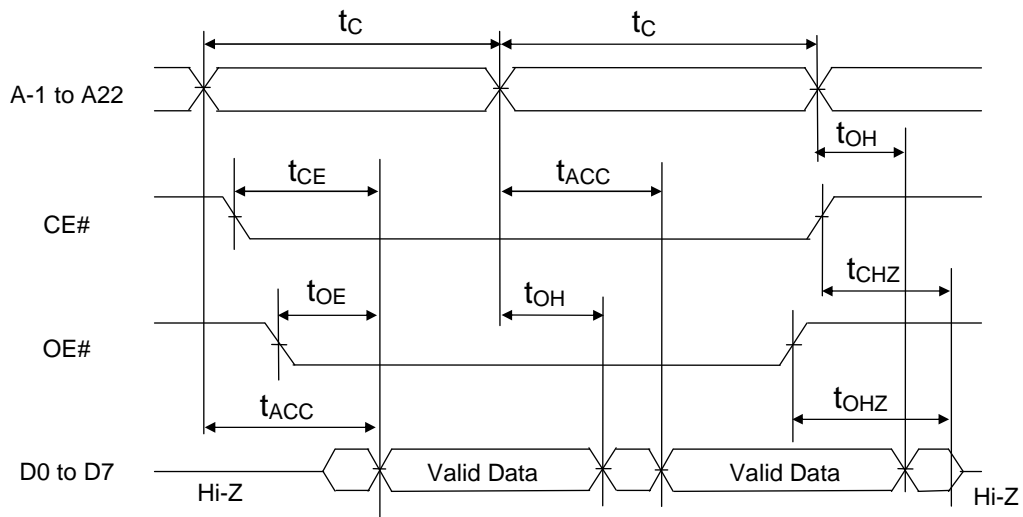
Output timing reference level ----- 1/2V_{CC}**Output load**

TIMING CHART (READ CYCLE)

16-Bit Read Mode (BYTE# = V_{IH})

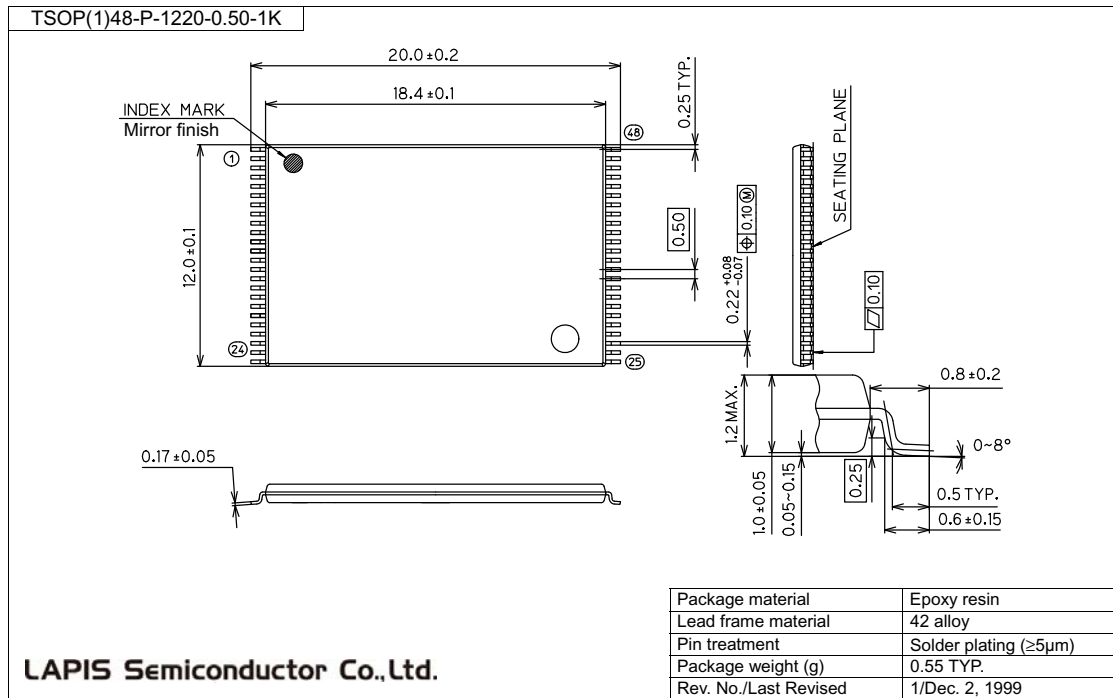


8-Bit Read Mode (BYTE# = V_{IL})



PACKAGE DIMENSIONS

(Unit: mm)

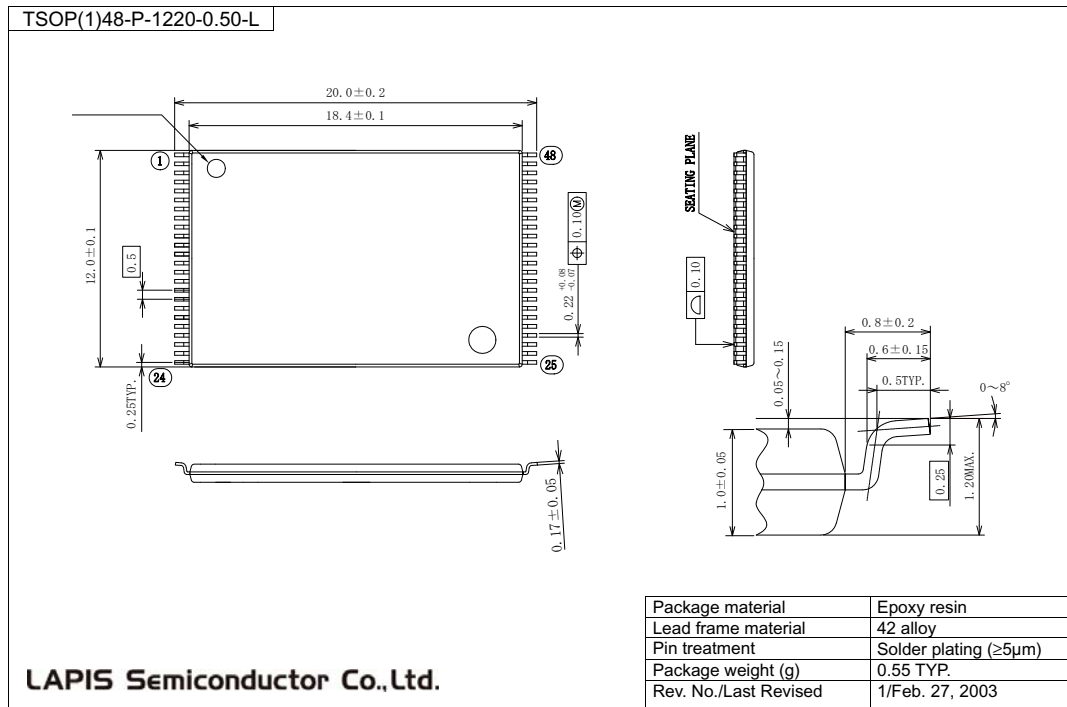


Notes for Mounting the Surface Mount Type Package

The surface mount type packages are very susceptible to heat in reflow mounting and humidity absorbed in storage.

Therefore, before you perform reflow mounting, contact ROHM's responsible sales person for the product name, package name, pin number, package code and desired mounting conditions (reflow method, temperature and times).

(Unit: mm)



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REVISION HISTORY

Document No.	Date	Page		Description
		Previous Edition	Current Edition	
FEDR27V12800J-02-01	July. 2002	–	–	Final edition 1
FEDR27V12800J-02-02	Jan. 2003	1, 4	1, 4	Change tC, tACC, tCE to 100ns
FEDR27V12800J-02-03	Jan. 2003	1	1	Change P/N to MR27V12800J-xxxTNE
FEDR27V12800J-02-04	Mar. 10, 2003	1, 4	1, 4	Added MR27V12800J-xxxTN
FEDR27V12800J-02-05	Jun. 6, 2003	1, 3, 4	1, 3, 4	1. Change Ta to 0°C 2. Added MR27V12800J-xxxTY, TYE
FEDR27V12800J-02-06	Jul. 9, 2004	3	3	Add P _D condition and I _{OS} = 10mA

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